

AS4C64M16D2A-25BCN vs AS4C64M16D2B-25BCN Comparison

Part Number & result Parameter	AS4C64M16D2A-25BCN	AS4C64M16D2B-25BCN	Comparison Result
Product Description	DDR2 SDRAM	DDR2 SDRAM	Same
Capacity	1Gb (64M x 16)	1Gb (64M x 16)	Same
Memory Organization	8M, x16bits, x8 banks	8M, x16bits, x8 banks	Same
Operating Power Supply	$V_{DD} \& V_{DDQ} = 1.8V$ (+/-0.1V)	$V_{DD} \& V_{DDQ} = 1.8V$ (+/-0.1V)	Same
Operating Temperature	Commercial (0°C to 85°C)	Commercial (0°C to 85°C)	Same
Clock Frequency	400MHz	400MHz	Same
Data Rate (MT/s)	800	800	Same
CAS Latency	5	5	Same
tRCD & tRP (ns)	12.5	12.5	Same
Average Refresh Period	8192 cycles/64ms	8192 cycles/64ms	Same
I/O Capacitance	CIO: 2.5pf to 3.5pf	CIO: 2.5pf to 3.5pf	Same
Pin to Pin Compatible	Pin to Pin Compatible		Same
AC/DC Characteristics	Same	Same	Meet JEDEC
IDD Specification			
IDD Spec conditions	$0C \leq T_c \leq 85C$ $V_{DD} = 1.8V \pm 0.1V$	$0C \leq T_c \leq 85C$ $V_{DD} = 1.8V \pm 0.1V$	Same
I_{DD0} (mA)	65	100	A version Better
I_{DD1} (mA)	75	115	A version Better
I_{DD2P} (mA)	10	30	A version Better
I_{DD2Q} (mA)	35	50	A version Better
I_{DD2N} (mA)	35	55	A version Better
I_{DD3Pf} (mA)	25	60	A version Better
I_{DD3Ps} (mA)	20	50	A version Better
I_{DD3N} (mA)	45	80	A version Better
I_{DD4R} (mA)	95	180	A version Better
I_{DD4W} (mA)	105	250	A version Better
I_{DD5} (mA)	100	165	A version Better
I_{DD6} (mA)	10	10	Same
I_{DD7} (mA)	170	100	B version Better
Package 84b FBGA	8 x 12.5 x 1.2mm Ball Array : 6.4 x 11.2x 0.8mm	8 x 12.5 x 1.2mm Ball Array : 6.4 x 11.2x 0.8mm	Ball matrix dimension same
Package Material	Pb and Halogen Free	Pb and Halogen Free	Same